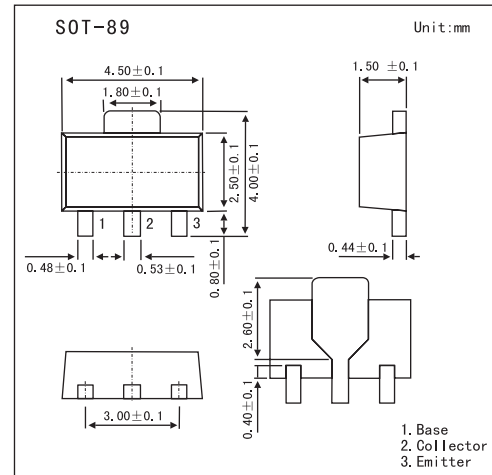


## PNP Silicon Epitaxial Transistor

## 2SB806

## ■ Features

- High collector to emitter voltage:  $V_{CE0} > -120V$ .

■ Absolute Maximum Ratings  $T_a = 25^\circ C$ 

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CB0}$	-120	V
Collector-emitter voltage	$V_{CE0}$	-120	V
Emitter-base voltage	$V_{EB0}$	-5	V
Collector current	$I_c$	-0.7	A
Collector current (pulse) *1	$I_{c(pu)}$	-1.2	A
Collector power dissipation	$P_c$	2	W
Junction temperature	$T_j$	150	$^\circ C$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ C$

\*1.  $PW \leq 10ms$ , duty cycle  $\leq 50\%$

■ Electrical Characteristics  $T_a = 25^\circ C$ 

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	$I_{CB0}$	$V_{CB} = -120V, I_E = 0$			-100	nA
Emitter cutoff current	$I_{EB0}$	$V_{EB} = -5V, I_c = 0$			-100	nA
DC current gain *	$h_{FE}$	$V_{CE} = -1V, I_c = -100mA$	90	200	400	
		$V_{CE} = -1V, I_c = -5.0mA$	45	200		
Collector-emitter saturation voltage *	$V_{CE(sat)}$	$I_c = -500mA, I_B = -50mA$		-0.4	-0.6	V
Base-emitter saturation voltage *	$V_{BE(sat)}$	$I_c = -500mA, I_B = -50mA$		-0.9	-1.5	V
Base-emitter voltage *	$V_{BE}$	$V_{CE} = -10V, I_c = -10mA$	-550	-620	-650	mV
Output capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1.0MHz$		14		pF
Transition frequency	$f_T$	$V_{CE} = -10V, I_E = 10mA$		75		MHz

\*  $PW \leq 350\mu s$ , duty cycle  $\leq 2\%$

■  $h_{FE}$  Classification

Marking	KR	KQ	KP
$h_{FE}$	90~180	135~270	200~400